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P-Channel 200 V (D-S) MOSFET

PRODUCT SUMMARY						
V _{DS} (V)	$R_{DS(on)}$ (m Ω)(Typ.)	I _D (A) ^a	Q _g (Typ.)			
- 200	310 at V _{GS} = - 10 V	- 10	30 nC			

FEATURES

- DT-Trench Power MOSFET
- 100 % R_g and UIS Tested
- · Low Gate Charge
- · Advanced trench process technology

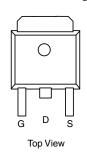


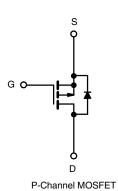
RoHS

APPLICATIONS

· Portable equipment and battery powered systems







ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)						
PARAMETER	SYMBOL	LIMIT	UNIT			
Drain-Source Voltage	V _{DS}	- 200				
Gate-Source Voltage	V _{GS}	± 20	V			
Continuous Drain Current /T 450 °C\2	T _C = 25 °C		- 10	А		
Continuous Drain Current (T _J = 150 °C) ^a	T _C = 100 °C	I _D	- 6			
Pulsed Drain Current ^b	I _{DM}	- 40				
Single Avalanche Energy	E _{AS}	510	mJ			
Mayimum Daway Dissinations	T _C = 25 °C	В	96	W		
Maximum Power Dissipation ^c	T _C = 100 °C	P _D	38			
Operating Junction and Storage Temperature F	T _J , T _{stg}	- 55 to +150	°C			

THERMAL RESISTANCE RATINGS					
PARAMETER	SYMBOL	LIMIT	UNIT		
Junction-to-Ambient (PCB Mount) ^d	R _{thJA}	65	°C/W		
Junction-to-Case (Drain)	R _{thJC}	1.3	C/VV		

Notes

- a. Calculated continuous current based on maximum allowablejunction temperature.
- b. Repetitive rating; pulse width limited by max. junction temperature.
- c. Pd is based on max. junction temperature, using junction-case thermal resistance.
- d. The value of R_{0JA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper,in a still air environment with Ta=25 °C.



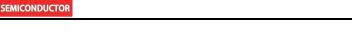
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static	<u>'</u>					_
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} = 0, I _D = - 250 μA	- 200			V
Gate-Source Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu\text{A}$	- 2		- 4	V
Gate-Source Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zara Cata Valtaga Drain Current	1	V _{DS} = - 200 V, V _{GS} = 0 V			- 1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 160 V, V _{GS} = 0 V, T _J = 55 °C			- 50	μΑ
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -10 \text{ V}$	- 10			Α
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 10 V, I _D = - 3.5 A		310	380	mΩ
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 5 V, I _D = - 3.5 A		10		S
Dynamic ^b						
Input Capacitance	C _{iss}			4090		pF
Output Capacitance	C _{oss}	$V_{DS} = -100 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		50		
Reverse Transfer Capacitance	C _{rss}	1		44		
Total Gate Charge	Q_g			30		
Gate-Source Charge	Q_{gs}	$V_{DS} = -100 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.5 \text{ A}$		7		nC
Gate-Drain Charge	Q_{gd}	1		10		
Gate Resistance	R _g	f = 1 MHz		3.3		Ω
Turn-On Delay Time	t _{d(on)}			17		
Rise Time	t _r	$V_{DD} = -100 \text{ V, R}_{L} = 1.5 \Omega$		95		
Turn-Off DelayTime	t _{d(off)}	$I_D \cong -3.5 \text{ A}, V_{GEN} = -10 \text{ V}, R_g = 3\Omega$		35		ns
Fall Time	t _f	1		50		
Drain-Source Body Diode Characterist	ics					
Continous Source-Drain Diode Current	I _S	T _C = 25 °C			- 10	А
Pulse Diode Forward Current	I _{SM}	_			- 40	
Body Diode Voltage	dy Diode Voltage V_{SD} $I_{S} = -1 \text{ A}$				- 1.2	V
Body Diode Reverse Recovery Time	t _{rr}	I _F = -3.5 A, dl/dt = 100 A/µs, T _I = 25 °C		120		ns
Body Diode Reverse Recovery Charge	Q _{rr}	$I_F = -3.5 \text{ A}, \text{ u/ut} = 100 \text{ A/}\mu\text{s}, \text{ IJ} = 25 \text{ C}$		25		nC

Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

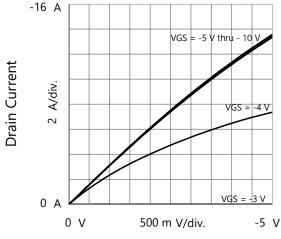
a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

b. Guaranteed by design, not subject to production testing.



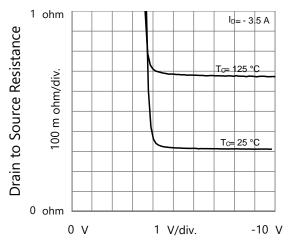
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TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

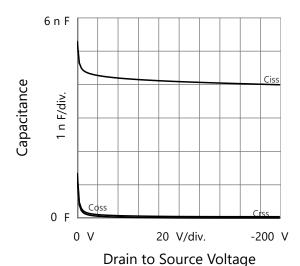


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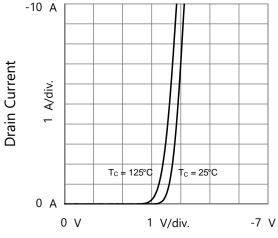
Drain to Source Voltage Output Characteristics



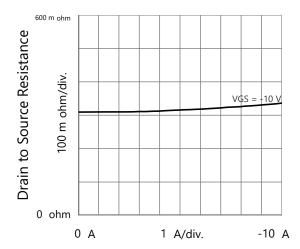
Gate to Source Voltage
Drain to Source Resistance vs. Gate to Source Voltage



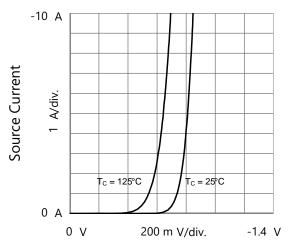
Capacitances



Gate to Source Voltage Transfer Characteristics



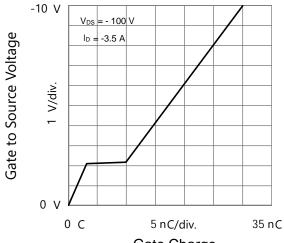
Drain Current
Drain to Source Resistance vs. Drain Current



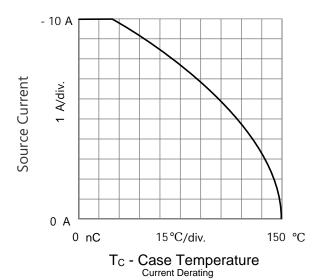
Source to Drain Voltage Body Diode Forward Characteristics



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Gate Charge
Gate to Source Voltage vs. GateCharge



- 100 A

10µS

10µS

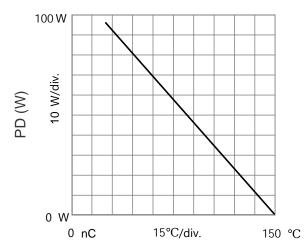
100µS

1mS

10mS

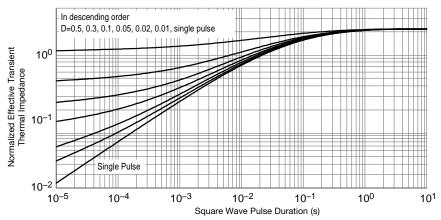
10m

Source to Drain Voltage Safe Operating Area, Junction-to-Ambient



T_C - Case Temperature

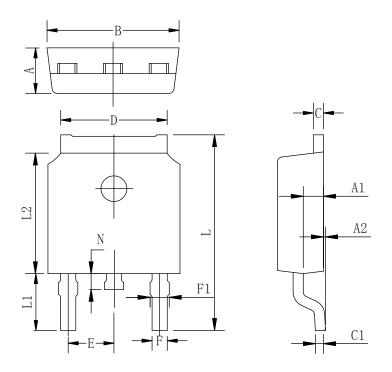
Power Derating



Normalized Thermal Transient Impedance, Junction-to-Case



TO-252-2L PACKAGE OUTLINE



COMMON DIMENSIONS (UNITS OF MEASURE=MILLIMETER)

Symbol	Min	Тур	Max
A	2.10	2.30	2.50
A1	0.88	1.01	1.16
A2	0.00	0.15	0.28
В	6.40	6.60	6.80
С	0.42	0.50	0.63
C1	0.42	0.50	0.63
D	5.08	5.32	5.65
Е	2.286 TYP		
F	0.63	0.76	0.89
F1	0.64	0.86	1.08
L	9.30	9.90	10.80
L1	2.4	2.8	3.6
L2	5.90	6.10	6.55
N	0.57	0.80	1.05

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